



**ELECTRONICS, INC.**  
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## NTE2559 (NPN) & NTE2560 (PNP) Silicon Complementary Transistors Darlington, Motor/Relay Driver

**Absolute Maximum Ratings:**

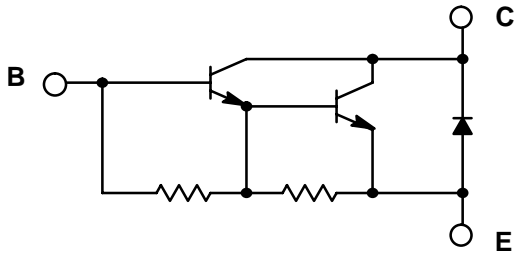
Collector–Base Voltage, $V_{CBO}$ .....	120V
Collector–Emitter Voltage, $V_{CEO}$ .....	120V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	16A
Pulsed .....	26A
Base Current, $I_B$ .....	1A
Collector Dissipation ( $T_{FL} = +25^{\circ}C$ ), $P_D$ .....	3W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	–55° to +150°C

**Electrical Characteristics:** ( $T_A = +25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 120V, I_E = 0$	–	–	10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 6V, I_C = 0$	–	–	10	mA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, R_{BE} = \infty$	120	–	–	V
DC Current Gain	$h_{FE}$	$V_{CE} = 4V, I_C = 8A$	2000	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 8A, I_B = 16mA$	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 8A, I_B = 16mA$	–	–	2.5	V

Note 1. For NTE2560, the polarity is reversed.

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(NPN)



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